

Pr: PLASMA ETCH METHOD FOR FORMING PLASMA ETCHED SILICON LAYER

JC542 U.S. PTO

09/442499

11/18/99

Enclosed are:

☒ 2 sheets of drawing(s) - formal.

☒ An assignment of the invention to **Chartered Semiconductor Manufacturing Ltd.**

☐ An associate power of attorney

The filing fee has been calculated as shown below:

(Col. 1)		(Col. 2)		OTHER THAN A SMALL ENTITY	
FOR:	NO. FILED	NO. EXTRA	RATE	FEE	
BASIC FEE				\$ 760.	
TOTAL CLAIMS	16 -20=	0	x 18 =	\$ 0.	
INDEP CLAIMS	3 -3=	0	x 78 =	\$ 0.	
MULTIPLE DEPENDENT CLAIM PRESENTED			+ 260 =		
			SUB TOTAL	\$ 760.	
			ASSIGNMENT	\$40.	
			TOTAL	\$ 800.	

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☒ Please charge my Deposit Account No. 19-0033 in the amount of \$ 800. A duplicate copy of this sheet is enclosed.

☒ The Commissioner is hereby authorized to charge payment of the following fees associated with this communication or credit any overpayment to Deposit Account No. 19-0033. A duplicate copy of this sheet is enclosed.

- ☒ Any additional filing fees required under 37 CFR §1.16.
- ☒ Any patent application processing fees under 37 CFR §1.17.

Respectfully submitted,

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